Exam.Code:0976 Sub. Code: 7431

## 2072

## M. Tech. (Microelectronics) Second Semester

## MIC-204: Advanced Memory Technology and Design

Time allowed: 3 Hours Max. Marks: 50

**NOTE:** Attempt <u>five</u> questions in all, including Question No. I which is compulsory and selecting two questions from each Section.

x-x-x

1. a) Write note on Hot-electron Injection.	(5x2)
b) What are Design Approaches in memory chip design?	(3A2)
c) Explain Redundancy techniques.	
d) Explain the On-chip testing Scheme. e) Explain the operation of DRAM cell.	
y ==-primar and operation of BRAWI cell.	
Section A	
2. a) Explain the basic operation of 1-T cell.	(5)
b) Explain the basic functioning of flash memory cells with diagram.	(5)
3. Draw and explain all the composition of basic memory circuit.	
4. Describe the role of V <sub>BB</sub> generator and reasons why its needed.	(10) (10)
Section B	(10)
5.a). Explain the basic chip configuration and operation of DRAM chip with diagram.	(5)
b). What is Address Multiplexing and its basic operation.	(5)
6. Explain the following with diagram:	
a). The address buffer	
b). Multi-divided data line	
c). Refresh-Relevant Circuits.	
7. Explain the Standard DR AM with Live 1	3+3+4)
7. Explain the Standard DRAM with block diagram and also explain its read-write cycle.	
	(10)